

Substitute form 1449/APTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/849,589
		Filing Date	May 20, 2004
		First Named Inventor	Adam Saxler
		Group Art Unit	2814
		Examiner Name	Wael M. Fahmy John C. Ingham
Sheet 1 of 1	Attorney Docket Number	5308-412	

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Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
9CI	1.	US-5,990,531		Taskar et al.	11-23-1999
9CI	2.	US-5,389,571		Takeuchi et al.	02-14-1995
9CI	3.	US-2003/0145784		Thompson et al.	08-07-2003
9CI	4.	US-2002/0079508		Yoshida	06-27-2002

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OTHER NON PATENT LITERATURE DOCUMENTS

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Examiner Signature	<i>John C. Ingham</i>	Date Considered	10/24/05
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First Named Inventor

Adam Saxler

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9ci	37.	United States Patent Application entitled "High Power Density and/or Linearity Transistors," Serial No. 11/005,107, filed December 6, 2004 (Attorney Docket No. 5308-511).		
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9ci	42.	United States Patent Application entitled "Composite Substrates of Conductive And Insulating or Semi-Insulating Group III-Nitrides For Group III-Nitride Devices," Serial No. 11/103,127, filed April 11, 2005 (Attorney Docket No. 5308-551).	
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FOREIGN PATENT DOCUMENTS

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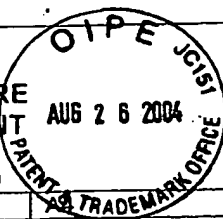
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		Number	Kind Code (if known)		
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9ci	107.	United States Patent Application entitled "Nitride-Based Transistors with a Protective Layer and a Low-Damage Recess and Methods of Fabrication Thereof," Serial No. 10/758,871, filed January 16, 2004 (Attorney Docket No. 5308-291).			
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Examiner Signature	<i>John Ingham</i>	Date Considered	10/24/05
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Substitute form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known			
		Application Number	10/849,589		
		Filing Date	May 20, 2004		
		First Named Inventor	Saxler		
		Group Art Unit	2811 2814		
		Examiner Name	Wael M. Fahmy John Ingham		
Sheet	A4	of	A4	Attorney Docket Number	5308-412

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
ACI	109.	United States Patent Application entitled "Nitride-Based Transistors and Methods of Fabrication Thereof Using Non-Etched Contact Recesses," Serial No. 10/617,843, filed July 11, 2003 (Attorney Docket No. 5308-248).	
ACI	110.	United States Patent Application entitled "Methods of Having Laterally Grown Active Region and Methods of Fabricating Same," filed July 26, 2004 (Attorney Docket No. 5308-374).	
ACI	111.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors Having Regrown Ohmic Contact Regions and Nitride-Based Transistors Having Regrown Ohmic Contact Regions," Serial No. 10/849,617, filed May 20, 2004 (Attorney Docket No. 5308-413)	
ACI	112.	United States Patent Application entitled, "Silicon Carbide on Diamond Substrates and Related Devices and Methods," (Cree Docket No. P0387).	

Examiner Signature	<i>John Ingham</i>	Date Considered	12/24/05
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